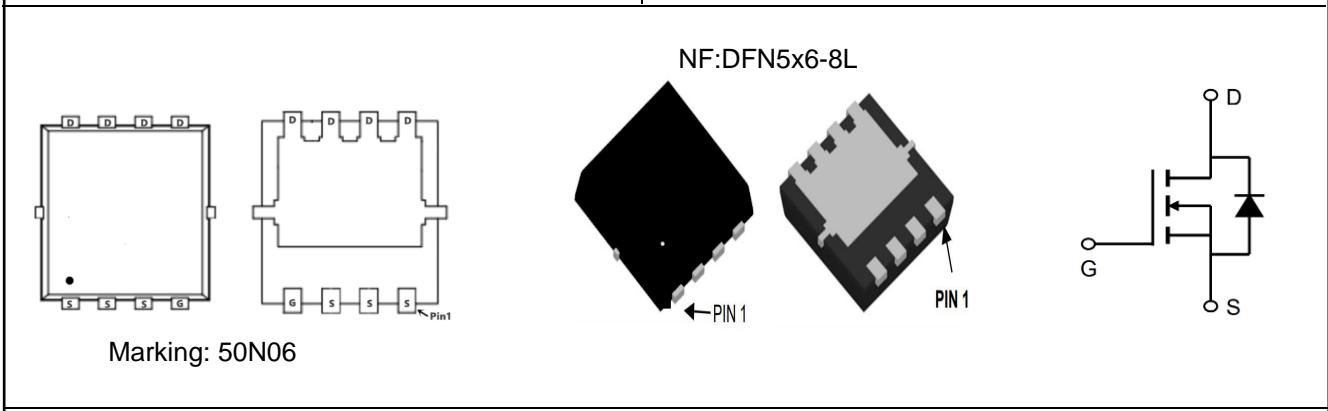


## TMG50N06NF

## N-Channel Enhancement Mosfet

<b>General Description</b> <ul style="list-style-type: none"> <li>• Low <math>R_{DS(ON)}</math></li> <li>• RoHS and Halogen-Free Compliant</li> </ul> <b>Applications</b> <ul style="list-style-type: none"> <li>• Load switch</li> <li>• PWM</li> </ul>	<b>General Features</b> <p><math>V_{DS} = 60V</math> <math>I_D = 50A</math></p> <p><math>R_{DS(ON)} = 11m\Omega</math> (typ.) @ <math>V_{GS} = 10V</math></p> <p>100% UIS Tested 100% <math>R_g</math> Tested</p> 
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### Absolute Maximum Ratings ( $T_c = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max.	Units
$V_{DSS}$	Drain-Source Voltage	60	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current $T_c = 25^\circ C$	50	A
		$29$	A
$I_{DM}$	Pulsed Drain Current <sup>note1</sup>	140	A
$E_{AS}$	Single Pulsed Avalanche Energy <sup>note2</sup>	36	mJ
$P_D$	Power Dissipation $T_c = 25^\circ C$	60	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	2.5	$^\circ C/W$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +175	$^\circ C$

**TMG50N06NF**
**N-Channel Enhancement Mosfet**
**Electrical Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$ , $I_D=250\mu\text{A}$	60	-	-	V
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{DS}=60\text{V}$ , $V_{GS}=0\text{V}$ ,	-	-	1.0	$\mu\text{A}$
$I_{\text{GSS}}$	Gate to Body Leakage Current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 20\text{V}$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	1.0	1.6	2.5	V
$R_{\text{DS}(\text{on})}$ note3	Static Drain-Source on-Resistance	$V_{GS}=10\text{V}$ , $I_D=20\text{A}$	-	11	14	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$ , $I_D=10\text{A}$	-	15	20	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=25\text{V}$ , $V_{GS}=0\text{V}$ , $f=1.0\text{MHz}$	-	930	-	pF
$C_{oss}$	Output Capacitance		-	230	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	8	-	pF
$Q_g$	Total Gate Charge	$V_{DS}=30\text{V}$ , $I_D=20\text{A}$ , $V_{GS}=10\text{V}$	-	22	-	nC
$Q_{gs}$	Gate-Source Charge		-	4.5	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	3.5	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=30\text{V}$ , $I_D=20\text{A}$ , $R_G=1.6\Omega$ , $V_{GS}=10\text{V}$	-	4.5	-	ns
$t_r$	Turn-on Rise Time		-	2.7	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	13.8	-	ns
$t_f$	Turn-off Fall Time		-	2.7	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_s$	Maximum Continuous Drain to Source Diode Forward Current	-	-	50	A	
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	-	180	A	
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS}=0\text{V}$ , $I_s=30\text{A}$	-	-	1.2	V
$t_{rr}$	Body Diode Reverse Recovery Time	$T_J=25^\circ\text{C}$ , $I_F=20\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$	-	18	-	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge		-	12	-	nC

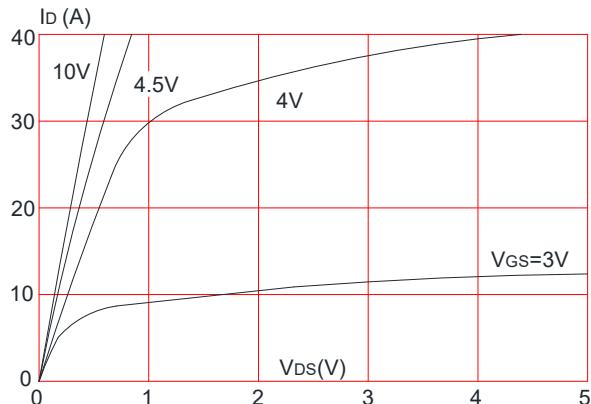
Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition:  $T_J=25^\circ\text{C}$ ,  $V_{DD}=30\text{V}$ ,  $V_G=10\text{V}$ ,  $R_G=25\Omega$ ,  $L=0.5\text{mH}$ ,  $I_{AS}=12\text{A}$ 

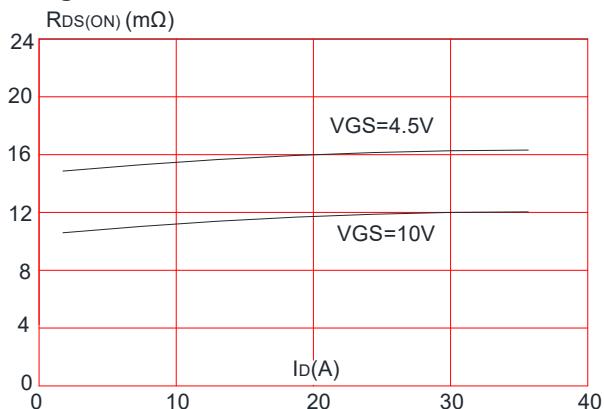
3. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 0.5\%$

## Typical Performance Characteristics

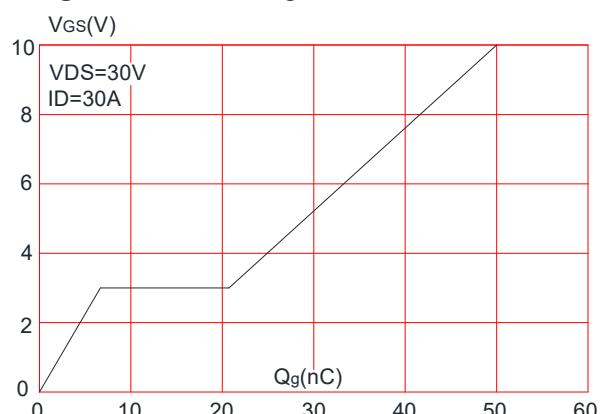
**Figure 1:** Output Characteristics



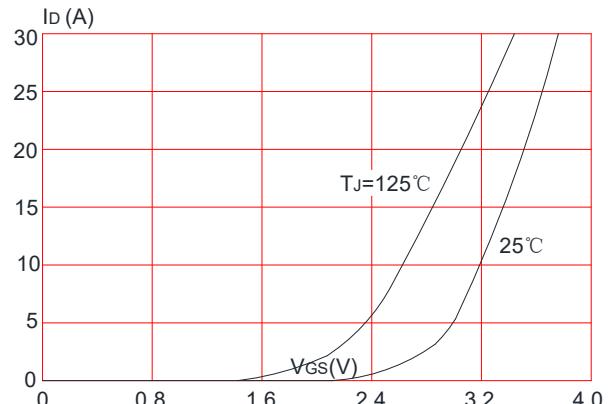
**Figure 3:** On-resistance vs. Drain Current



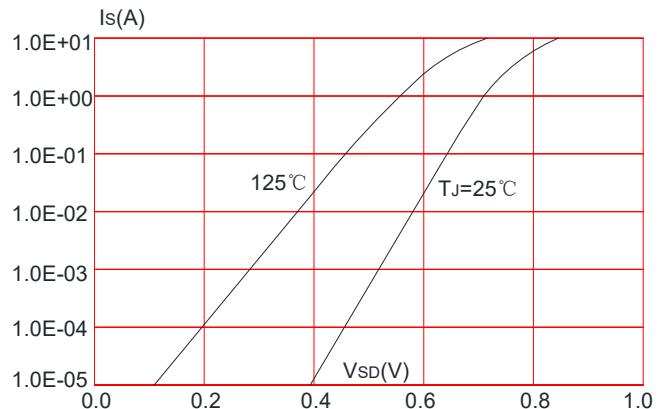
**Figure 5:** Gate Charge Characteristics



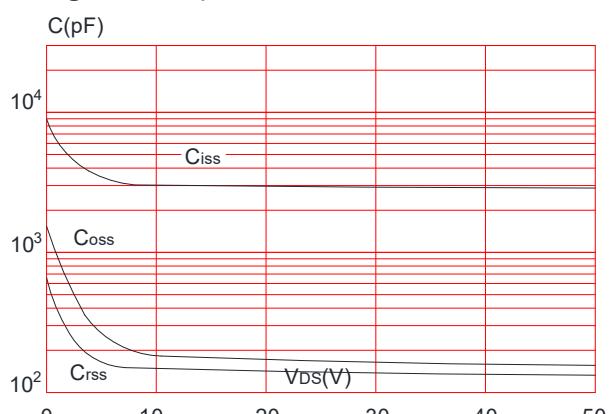
**Figure 2:** Typical Transfer Characteristics



**Figure 4:** Body Diode Characteristics



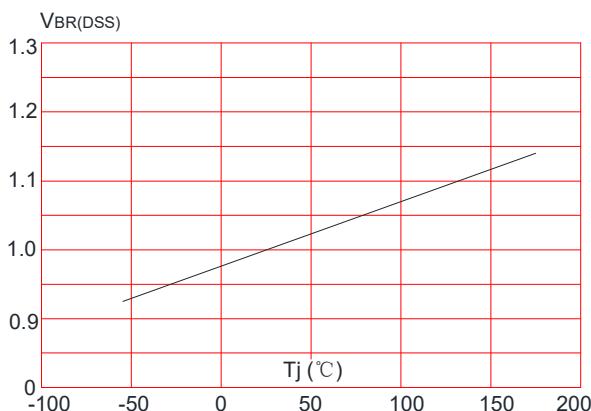
**Figure 6:** Capacitance Characteristics



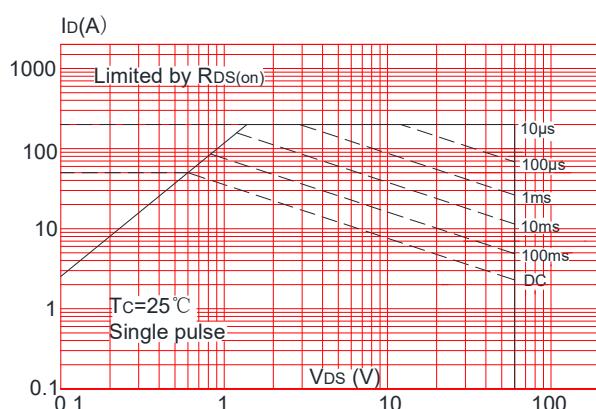
## TMG50N06NF

## N-Channel Enhancement Mosfet

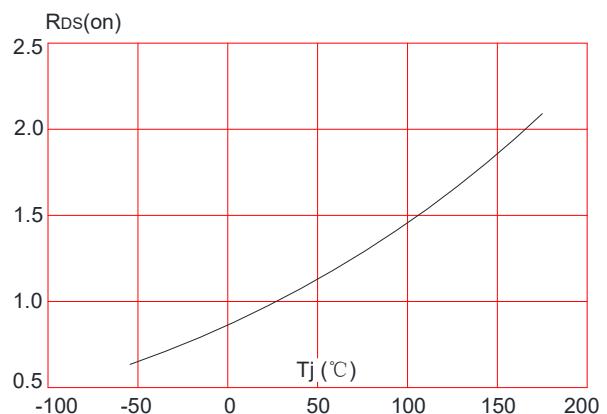
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



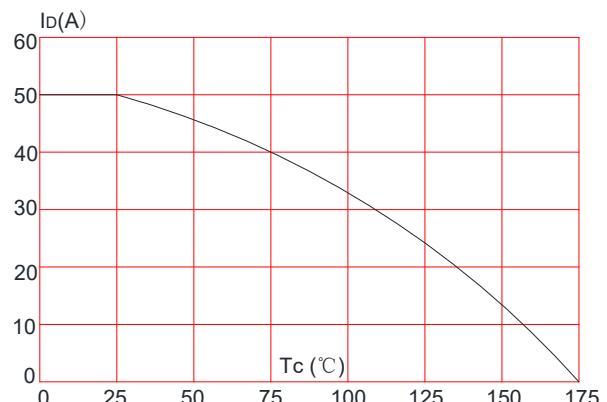
**Figure 9:** Maximum Safe Operating Area



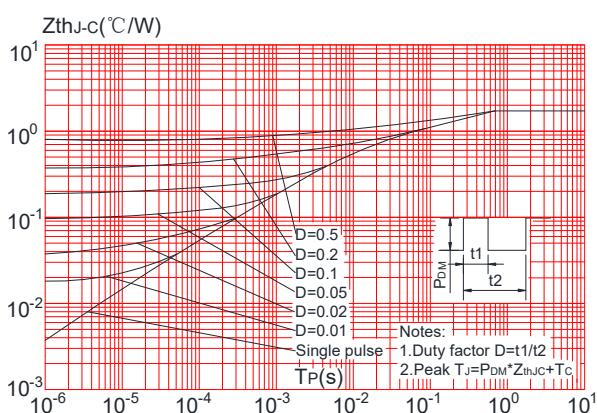
**Figure 8:** Normalized on Resistance vs. Junction Temperature



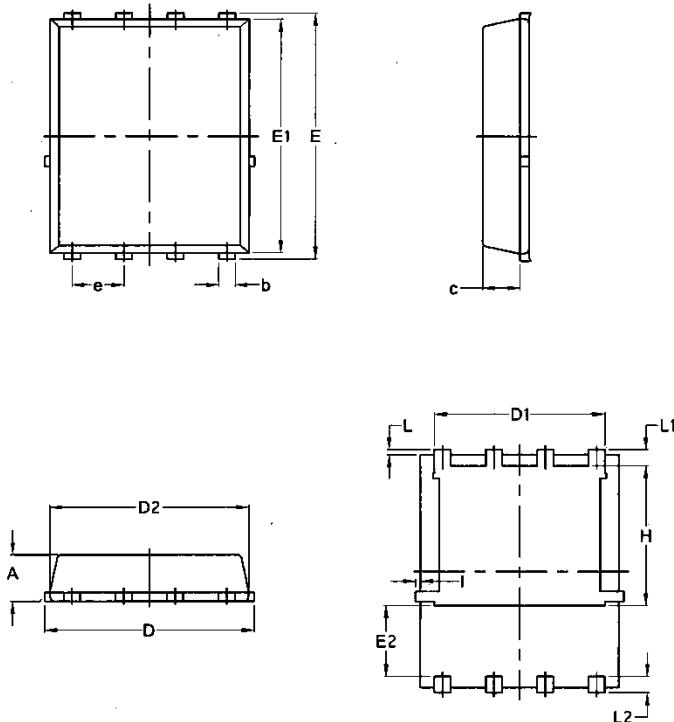
**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature



**Figure 11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case



## Package Mechanical Data:DFN5x6-8L



Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070